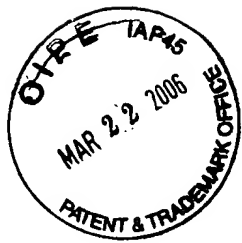


IFW



Docket No.: M4065.0439/P439  
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:  
Joseph E. Geusic et al.

Application No.: 09/855,532

Confirmation No.: 9772

Filed: May 16, 2001

Art Unit: 2828

For: METHOD OF FORMING MIRRORS BY  
SURFACE TRANSFORMATION OF  
EMPTY SPACES IN SOLID STATE  
MATERIALS AND STRUCTURES  
THEREON (AS AMENDED)

Examiner: A. Rodriguez

**INFORMATION DISCLOSURE STATEMENT (IDS)**

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Dear Sir:

Pursuant to 37 CFR 1.56, 1.97 and 1.98, the attention of the Patent and Trademark Office is hereby directed to the references listed on the attached PTO/SB/08. It is respectfully requested that the information be expressly considered during the prosecution of this application, and that the references be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

This Information Disclosure Statement is filed before the mailing date of a first Office Action after the filing of a Request for Continued Examination under 37 CFR 1.114 (37 CFR 1.97(b)(4)).

Application No.: 09/855,532



Docket No.: M4065.0439/P439

In accordance with 37 CFR 1.97(g), the filing of this Information Disclosure Statement shall not be construed to mean that a search has been made or that no other material information as defined in 37 CFR 1.56(a) exists. In accordance with 37 CFR 1.97(h), the filing of this Information Disclosure statement shall not be construed to be an admission that any patent, publication or other information referred to therein is "prior art" for this invention unless specifically designated as such.

It is submitted that the Information Disclosure Statement is in compliance with 37 CFR 1.98 and the Examiner is respectfully requested to consider the listed references.

The Director is hereby authorized to charge any deficiency in the fees filed, asserted to be filed or which should have been filed herewith (or with any paper hereafter filed in this application by this firm) to our Deposit Account No. 04-1073, under Order No. M4065.0439/P439.

Dated: March 22, 2006

Respectfully submitted,

By 

Thomas J. D'Amico

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Gabriela I. Coman

Registration No.: 50,515

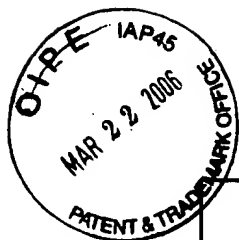
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Attorneys for Applicant



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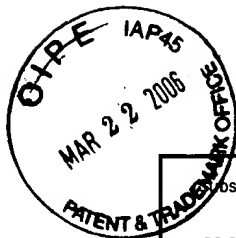
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				Application Number	09/855,532-Conf. #9772
				Filing Date	May 16, 2001
				First Named Inventor	Joseph E. Geusic
				Art Unit	2828
				Examiner Name	A. Rodriguez
				Attorney Docket Number	M4065.0439/P439
Sheet	1	of	10		

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. 1	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code 2 (if known)			
	AA	3,497,455	02-1970	Ahr	
	AB	4,241,359	12-1980	Izumi, et al.	
	AC	4,314,595	02-1982	Yamamoto, et al.	
	AD	4,589,928	05-1986	Dalton	
	AE	4,717,681	01-1988	Curran	
	AF	4,756,956	07-1988	Nagai, et al.	
	AG	4,962,051	10-1990	Liaw	
	AH	4,962,058	10-1990	Cronin, et al.	
	AI	4,992,321	02-1991	Kandachi, et al.	
	AJ	5,055,426	10-1991	Manning	
	AK	5,098,852	03-1992	Niki, et al.	
	AL	5,110,754	05-1992	Lowrey, et al.	
	AM	5,250,459	10-1993	Lee	
	AN	5,404,029	04-1995	Husher, et al.	
	AO	5,426,061	06-1995	Sopori	
	AP	5,443,661	08-1995	Oguro, et al.	
	AQ	5,461,243	10-1995	Ek, et al.	
	AR	5,471,180	11-1995	Brommer, et al.	
	AS	5,526,449	06-1996	Meade, et al.	
	AT	5,527,739	06-1996	Parrillo, et al.	
	AU	5,599,745	02-1997	Reinberg	
	AV	5,639,684	06-1997	Kwok	
	AW	5,646,053	07-1997	Schepis	
	AX	5,661,044	08-1997	Holland, et al.	
	AY	5,691,230	11-1997	Forbes	
	AZ	5,739,796	04-1998	Jasper, et al.	
	AA1	5,759,898	06-1998	Ek, et al.	
	AB1	5,773,152	06-1998	Okonogi	
	AC1	5,789,859	08-1998	Watkins, et al.	
	AD1	5,798,559	08-1998	Bothra	
	AE1	5,811,870	09-1998	Bhattacharyya, et al.	
	AF1	5,834,824	11-1998	Shepherd, et al.	
	AG1	5,840,590	11-1998	Myers, Jr., et al.	
	AH1	5,858,869	01-1999	Chen, et al.	
	AI1	5,866,204	02-1999	Robbie, et al.	
	AJ1	5,879,996	03-1999	Forbes	
	AK1	5,903,041	05-1999	La Fleur, et al.	
	AL1	5,953,625	09-1999	Bang	
	AM1	5,962,910	10-1999	Hawley, et al.	
	AN1	5,963,817	10-1999	Chu, et al.	
	AO1	5,969,983	10-1999	Thakur, et al.	
	AP1	5,973,380	10-1999	Cutter, et al.	
	AQ1	5,994,776	11-1999	Fang, et al.	
	AR1	5,997,378	12-1999	Dynka, et al.	
	AS1	5,999,308	12-1999	Nelson, et al.	
Examiner Signature				Date Considered	



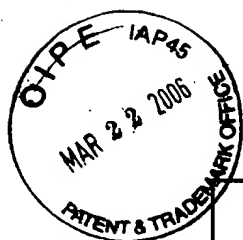
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				Art Unit	2828
				Examiner Name	A. Rodriguez
Sheet	2	of	10	Attorney Docket Number	M4065.0439/P439

	AT1	6,001,711	12-1999	Hashimoto	
	AU1	6,013,970	01-2000	Nishikawa, et al.	
	AV1	6,016,000	01-2000	Moslehi	
	AW1	6,016,001	01-2000	Sanchez, et al.	
	AX1	6,022,793	02-2000	Wijaranakula, et al.	
	AY1	6,054,808	04-2000	Watkins, et al.	
	AZ1	6,057,224	05-2000	Bothra	
	AA2	6,069,064	05-2000	Cutter, et al.	
	AB2	6,075,640	06-2000	Nelson	
	AC2	6,077,792	06-2000	Farrar	
	AD2	6,083,324	07-2000	Henley, et al.	
	AE2	6,084,814	07-2000	Casper, et al.	
	AF2	6,088,282	07-2000	Loughmiller, et al.	
	AG2	6,093,623	07-2000	Forbes	
	AH2	6,093,624	07-2000	Letavic, et al.	
	AI2	6,097,077	08-2000	Gordon, et al.	
	AJ2	6,113,758	09-2000	De Nora, et al.	
	AK2	6,127,777	10-2000	Watkins, et al.	
	AL2	6,136,666	10-2000	So	
	AM2	6,139,626	10-2000	Norris, et al.	
	AN2	6,146,925	11-2000	Dennison	
	AO2	6,172,456	01-2001	Cathey, et al.	
	AP2	6,174,784	01-2001	Forbes	
	AQ2	6,202,065	03-2001	Wills	
	AR2	6,204,145	03-2001	Noble	
	AS2	6,206,065	03-2001	Robbie, et al.	
	AT2	6,228,694	05-2001	Doyle, et al.	
	AU2	6,239,187	05-2001	Hatke, et al.	
	AV2	6,248,422	06-2001	Robbie, et al.	
	AW2	6,251,751	06-2001	Chu, et al.	
	AX2	6,252,293	06-2001	Seyyedy, et al.	
	AY2	6,255,156	07-2001	Forbes, et al.	
	AZ2	6,261,876	07-2001	Crowder, et al.	
	AA3	6,274,460	08-2001	Delgado, et al.	
	AB3	6,277,728	08-2001	Ahn	
	AC3	6,284,675	09-2001	Jin, et al.	
	AD3	6,288,437	09-2001	Forbes, et al.	
	AE3	6,291,871	09-2001	Dennison	
	AF3	6,309,950	10-2001	Forbes	
	AG3	6,315,826	11-2001	Muramatsu	
	AH3	6,323,536	11-2001	Cutter, et al.	
	AI3	6,338,805	01-2002	Anderson	
	AJ3	6,339,011	01-2002	Gonzalez, et al.	
	AK3	6,344,373	02-2002	Bhattacharyya, et al.	
	AL3	6,351,425	02-2002	Porter	
	AM3	6,368,938	04-2002	Usenko	
	AN3	6,376,336	04-2002	Buynoski	
	AO3	6,377,070	04-2002	Forbes	

Examiner Signature		Date Considered	
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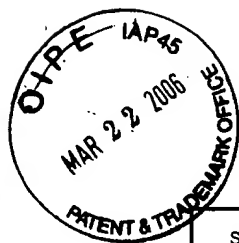
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				Examiner Name	A. Rodriguez
Sheet	3	of	10	Attorney Docket Number	M4065.0439/P439

AP3	6,383,924	05-2002	Farrar, et al.	
AQ3	6,387,824	05-2002	Aoi, et al.	
AR3	6,391,738	05-2002	Moore	
AS3	6,423,582	07-2002	Fischer, et al.	
AT3	6,423,613	07-2002	Geusic	
AU3	6,424,001	07-2002	Forbes, et al.	
AV3	6,436,187	08-2002	Patel, et al.	
AW3	6,444,534	09-2002	Maszara	
AX3	6,444,558	09-2002	Cutter, et al.	
AY3	6,448,601	09-2002	Forbes, et al.	
AZ3	6,452,713	09-2002	White	
AA4	6,456,149	09-2002	Cutter, et al.	
AB4	6,458,630	10-2002	Daubenspeck, et al.	
AC4	6,461,933	10-2002	Houston	
AD4	6,478,883	11-2002	Tamatsuka, et al.	
AE4	6,495,395	12-2002	Reinberg	
AF4	6,496,034	12-2002	Forbes, et al.	
AG4	6,498,056	12-2002	Motsiff, et al.	
AH4	6,509,623	01-2003	Zhao	
AI4	6,525,399	02-2003	Cutter, et al.	
AJ4	6,531,727	03-2003	Forbes, et al.	
AK4	6,538,330	03-2003	Forbes	
AL4	6,541,356	04-2003	Fogel, et al.	
AM4	6,541,811	04-2003	Thakur, et al.	
AN4	6,542,682	04-2003	Cotteverte, et al.	
AO4	6,559,491	05-2003	Forbes, et al.	
AP4	6,566,682	05-2003	Forbes	
AQ4	6,579,738	06-2003	Farrar, et al.	
AR4	6,582,512	06-2003	Geusic, et al.	
AS4	6,583,437	06-2003	Mizuno, et al.	
AT4	6,589,334	07-2003	John, et al.	
AU4	6,593,625	07-2003	Christiansen, et al.	
AV4	6,597,203	07-2003	Forbes	
AW4	6,630,713	10-2003	Geusic	
AX4	6,630,724	10-2003	Marr	
AY4	6,649,476	11-2003	Forbes	
AZ4	6,656,822	12-2003	Doyle, et al.	
AA5	6,657,277	12-2003	Hsieh	
AB5	6,674,667	01-2004	Forbes	
AC5	6,740,913	05-2004	Doyle, et al.	
AD5	6,943,065	09-2005	Bhattacharyya, et al.	
AE5	2002/0001965	01/2002	Forbes	
AF5	2002/0048968	04/2002	Ahn	
AG5	2002/0062782	05/2002	Norris, et al.	
AH5	2002/0070419	06/2002	Farrar, et al.	
AI5	2002/0070421	06/2002	Ashburn	
AJ5	2002/0076896	06/2002	Farrar, et al.	
AK5	2002/0079557	06/2002	Ahn, et al.	

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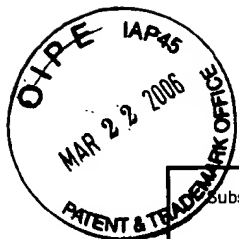
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				Art Unit	2828
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Sheet	4	of	10	Attorney Docket Number	M4065.0439/P439

	AL5	2002/0175330	11/2002	Geusic, et al.	
	AM5	2002/0182837	12/2002	Daubenspeck, et al.	
	AN5	2002/0185686	12/2002	Christiansen, et al.	
	AO5	2003/0027406	02/2003	Malone	
	AP5	2003/0042534	08/2001	Bhattacharyya	
	AQ5	2003/0042627	03/2003	Farrar, et al.	
	AR5	2003/0071324	05/2003	Motsiff, et al.	
	AS5	2003/0075438	04/2003	Dalmia, et al.	
	AT5	2003/0157780	08/2003	Farrar, et al.	
	AU5	2003/0190796	10/2003	Geusic	
	AV5	2003/0201468	10/2003	Christiansen, et al.	
	AW5	2003/0218189	11/2003	Christiansen, et al.	
	AX5	2003/0227072	12/2003	Forbes	
	AY5	2004/0171196 A1	09/2004	Walitzki	
	AZ5	2004/0176483 A1	09/2004	Geusic	
	AA6	2004/0266220 A1	12/2004	Ahn, et al.	
	AB6	2005/0020094 A1	01/2005	Forbes, et al.	
	AC6	2005/0023638 A1	02/2005	Bhattacharyya, et al.	
	AD6	2005/0070036 A1	05/2005	Geusic, et al.	
	AE6	2005/0089292 A1	04/2005	Kinoshita	

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T
		Country Code <sup>3</sup> -Number <sup>4</sup> -Kind Code <sup>5</sup> (if known)				
	BA	EP 1030196	08/2000			
	BB	EP 1085352	03/2001			
	BC	JP 2001-093887	04/2001			
	BD	EP 434984	09/1991			
	BE	WO 98/35248	08/1998			
	BF	WO 02/097982	12/2002			

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. <sup>1</sup> Applicant's unique citation designation number (optional). <sup>2</sup> See Kinds Codes of USPTO Patent Documents at [www.uspto.gov](http://www.uspto.gov) or MPEP 901.04. <sup>3</sup> Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). <sup>4</sup> For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. <sup>5</sup> Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. <sup>6</sup> Applicant is to place a check mark here if English language Translation is attached.

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
	CA	ABE, T.; Nakano, M.; Itho, T.; Takei, T.; Uchiyama, A.; Yoshizawa, K.; Nakazato, Y., Silicon Wafer-Bonding Process Technology for SOI Structures, Extended Abstracts of the 22nd Int'l Conference on Solid State Devices and Materials, Sendai, (1990) 853-856.	
	CB	ABELMANN, Leon; Lodder, C., Oblique evaporation and surface diffusion, Thin Solid Films 305 (1997) 1-21.	
	CC	ASOH, Hidetaka; Nishio, K.; Nakao, M.; Yokoo, A.; Tamaura, T.; Masuda, H., Fabrication of ideally ordered anodic porous alumina with 63 nm hole periodicity using sulfuric acid, J. Vac.	
Examiner Signature			Date Considered



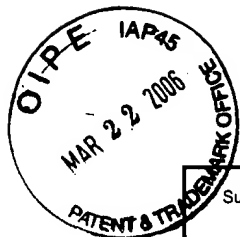
PTO/SB/08a/b (07-05)

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			Examiner Name	A. Rodriguez	
Sheet	5	of	10	Attorney Docket Number	M4065.0439/P439

		Sci. Technol. B 19(2) Mar/April (2001) 569-572.	
CD	AUBERTON-HERVE, A.J., SOI: Materials to Systems, Int'l Electron Devices Meeting, Technical Digest (1996) 3-10.		
CE	AUTUMN, Kellar; Liang, Y.A.; Hsieh, S.T.; Zesch, W.; Chan, W.P.; Kenny, T.W.; Fearing, R.; Full, R.J., Adhesive force of a single gecko foot-hair, Nature, 405, Jun 8, 2000, 681-685.		
CF	AUTUMN, Kellar; Sitti, M.; Liang, Y.A.; Peattie, A.M.; Hansen, W.R.; Sponberg, S.; Kenny, T.W.; Fearing, R.; Israelachvili, J.N.; Full, R.J., Evidence for van der Waals adhesion in gecko setae, Proc. of the National Academy of Science, 99(19) Sep 17, 2002, 12252-12256.		
CG	BAGINSKI, Thomas A., Back-side Germanium Ion Implantation Gettering of Silicon, J. Electrochem. Soc.: Solid-State Science and Technology, 135(7) Jul 1988, 1842-1843.		
CH	BANHART, John, Manufacture, characterization and application of cellular metals and metal foams, Progress in Materials Science 46 (2001) 559-632.		
CI	BANHART, John; Weaire, D., On the Road Again: Metal Foams Find Favor, Physics Today, Jul 2002, 37-42.		
CJ	BEAUVAIS, Jacques; Lavallee, E.; Drouin, D.; Turcotte, D., Nano-Imprint Lithography Using Materials Fabricated by SIDWELL Process, J. Vac. Sci. Technol. B, 17, 2957 (1999).		
CK	BELFORD, Rona E.; Zhao, W.; Potashnik, J.; Liu, Q.; Seabaugh, A., Performance-Augmented CMOS Using Back-End Uniaxial Strain, IEEE 60th DRC., Conference Digest, 2002, 41-42.		
CL	BERTI, M.; Mazzi, G.; Calagnile, L.; Drigo, A.V.; Merli, P.G.; Migliori, A., Composition and structure of Si-Ge layers produced by ion implantation and laser melting, J. Mater. Res., 6(10) Oct 1991, 2120-2126.		
CM	BERTI, M.; Mazzi, G.; Drigo, A.V.; Migliori, A.; Jannitti, E.; Nicoletti, S., Laser induced epitaxial regrowth of Si <sub>1-x</sub> Ge <sub>x</sub> /Si layers produced by Ge ion implantation, Applied Surface Science 43 (1989) 158-164.		
CN	BHATTACHARYYA, A.; Bass, R.; Tice, W.; Baxter, R.; Derenthal, T., Physical and Electrical Characteristics of LPCVD Si-Rich Nitride, J. Electrochem. Soc., 131(11) 469C.		
CO	BIALAS, F.; Winkler, R.; Dietrich, H., Intrinsic gettering of 300 mm CZ wafers, Microelectronic Engineering 56 (2001) 157-163.		
CP	BINNS, M.J.; Banerjee, A.; Wise, R.; Myers, D.J.; McKenna, T.A., The Realization of Uniform and Reliable Intrinsic Gettering in 200mm p- and p/p- Wafers for a Low Thermal Budget 0.18µm Advanced CMOS Logic Process, Solid State Phenomena, Vols. 82-84 (2002) 387-392.		
CQ	BIRNER, A.; Gruning, U.; Ottow, S.; Schneider, A.; Muller, F.; Lehmann, V.; Foll, H.; Gosele, U., Macroporous Silicon: A Two-Dimensional Photonic Bandgap Material Suitable for the Near-Infrared Spectral Range, Phys. Stat. Sol. (a) 165 (1998) 111-117.		
CR	BIRNER, Albert; Wehrspohn, R.B.; Gosele, U.M.; Busch, K., Silicon-Based Photonic Crystals, Adv. Mater. 13(6) Mar 16, 2001, 377-388.		
CS	BLANCO, Alvaro, et al., Large-scale synthesis of a silicon photonic crystal with a complete three-dimensional bandgap near 1.5 micrometres, Nature, 405, May 25, 2000, 437-440.		
CT	BLANFORD, Christopher; Yan, H.; Schroden, R.C.; Al-Daous, M.; Stein, A., Gems of Chemistry and Physics: Macroporous Metal Oxides with 3D Order, Adv. Mater. 13(6) Mar 16, 2001, 401-407.		
CU	BRONNER, Gary; Plummer, J.D.; Physical Modeling of Backside Gettering, Mat. Res. Soc. Symposia Proceedings Vol. 36, Boston, Nov 27-30, 1984, 49-54.		
CV	BROWN, Chappell, Bonding twist hints at universal substrate, EETimes (1997) 2 pgs.		
CW	BRUEL, Michel; Aspar, B.; Auberton-Herve, A.-J., Smart-Cut: A New Silicon On Insulator Material Technology Based on Hydrogen Implanatation and Wafer Bonding, Jpn. J. Appl. Phys., Vol. 36 (Mar 1997) Pt. 1, No. 3B, 1636-1641.		
CX	CRC Handbook of Chemistry and Physics, 49th ed. (c1968) The Chemical Rubber Pub. Co., Cleveland, OH, E-61.		
Examiner Signature		Date Considered	



PTO/SB/08a/b (07-05)

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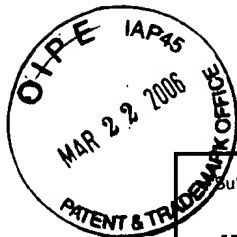
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			Filing Date	May 16, 2001	
			First Named Inventor	Joseph E. Geusic	
			Art Unit	2828	
			Examiner Name	A. Rodriguez	
Sheet	6	of	10	Attorney Docket Number	M4065.0439/P439

CY	CHEN, Xiangdong; Ouyang, Q.; Liu, K.-C.; Shi, Z.; Tasch, A.; Banerjee, S., Vertical P-MOSFETS with heterojunction between source/drain and channel, 58th Device Research Conference Digest, Jun 19-21, 2000, Denver, CO, 25-26.
CZ	CHILTON, B.T.; Robinson, B.J.; Thompson, D.A.; Jackman, T.E.; Baribeau, J.-M., Solid phase epitaxial regrowth of Si <sub>1-x</sub> Ge <sub>x</sub> /Si strained-layer structures amorphized by ion implantation, Appl. Phys. Lett. 54(1) Jan 2, 1989, 42-44.
CA1	CHOE, K.S.; Jang, B.N., Minority-carrier lifetime optimization in silicon MOS devices by intrinsic gettering, J. of Cryst. Growth 218 (2000) 239-244.
CB1	CHOU, Stephen Y.; Krauss, P.R., Imprint Lithography with Sub-10 nm Feature Size and High Throughput, Microelectronic Engineering 35 (1997) 237-240.
CC1	CHOU, Stephen Y.; Krauss, P.R.; Zhang, W.; Guo, L.; Zhuang, L., Sub-10 nm imprint lithography and applications, J. Vac. Sci. Technol. B 15(6) Nov/Dec 1997, 2897-2904.
CD1	CLARK, Don, Intel Unveils New Technology For Creating Tiny Transistors, The Wall Street Journal, Aug 13, 2002, P.1.
CE1	CLIFTON, P.A.; Routley, P.R.; Gurry, P.K.; O'Neill, A.G.; Carter, J.A.; Kemhadjian, H.A., A Process for Strained Silicon n-Channel HMOSFETS, Proc. of the 26th European Solid State Device Research Conference, Sep 9-11, 1996, Bologna, Italy, 519-522.
CF1	COLGAN, M.J.; Brett, M.J., Field emission from carbon and silicon films with pillar microstructure, Thin Solid Films 389 (2001) 1-4.
CG1	CORNELL Demonstrates a Universal Substrate, Compound Semiconductor, Mar/Apr 1997, 3(2) 27
CH1	DAS, B.; McGinnis, S.; Miller, A., Template Based Semiconductor Nanostructure Fabrication and their Applications, Invited Paper, 11th International Workshop in the Physics of Semiconductor Devices (2001) D.1.1.
CI1	DEVASAHAYAM, Adrian J.; Agatic, I.; Zaritsky, I.; Druz, B.; Hegde, H.; Das, S.R.; LaFramboise, S., Material Properties of Ion Beam Deposited Oxides for the Opto-Electronic Industry, 10th Canadian Semiconductor Technology Conference, Ottawa, Aug. 13-17, 2001, Th1.3, 185.
CJ1	DUBBLEDAY, Wadad B.; Kavanagh, K.L., Oscillatory Strain Relaxation in Solid Phase Epitaxially Regrown Silicon on Sapphire, Lattice Mismatched Thin Films, E.A. Fitzgerald, Ed., The Minerals, Metals & Materials Society Pub., c1999, 13-17.
CK1	EDRINGTON, Alexander C., et al., Polymer-Based Photonic Crystals, Adv. Mater., 13(6) Mar 16, 2001, 421-425.
CL1	FISCHETTI, M.V.; Laux, S.E., Band structure, deformation potentials, and carrier mobility in strained Si, Ge, and SiGe alloys, J. Appl. Phys. 80 (4) Aug 15, 1996, 2234-2252.
CM1	FOURNEL, F.; Moriceau, H.; Aspar, B.; Magnea, N.; Eymery, J.; Rousseau, K.; Rouviere, J.L., Ultra High Precision of the Tilt/Twist Misorientation Angles in Silicon/Silicon Direct Wafer Bonding, Electronic Materials Conference Abstract, Jun 2002, 9.
CN1	GARCIA, G.A.; Reedy, R.E.; Burgener, M.L., High-Quality CMOS in Thin (100 nm) Silicon on Sapphire, IEEE Electron Device Letters, 9(1) Jan 1988, 32-34.
CO1	GODBOLE, H.; Haddad, H.; Forbes, L., An investigation of bulk stacking faults in silicon using photocapacitance transient spectroscopy, Materials Letters, 8 (6, 7) Jul 1989, 201-203.
CP1	GONG, S.S.; Schroder, D.K., Implantation gettering in silicon, Solid-State Electronics, 30(2) (1987) 209-211.
CQ1	GRAF, D.; Lambert, U.; Schmolke, R.; Wahlich, R.; Siebert, W.; Daub, E.; Ammon, W.V., 300 mm EPI PP- wafer: Is there sufficient gettering?, Electrochemical Soc. Proc. Vol. 2000-17, 319-330.
CR1	HADDAD, H.; Forbes, L.; Burke, P.; Richling, W., Carbon Doping Effects on Hot Electron Trapping, IEEE Electron Devices Soc. 28th Ann. Proc. Mar 27-29, 1990, New Orleans, LA, 288-289.

Examiner Signature		Date Considered	
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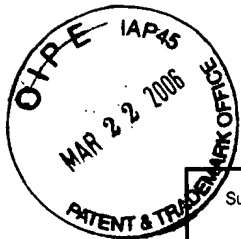
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				Examiner Name	A. Rodriguez
Sheet	7	of	10	Attorney Docket Number	M4065.0439/P439

	CS1	HADDAD, H.; Forbes, L., Electrical activity of bulk stacking faults in silicon, Materials Letters, 7(3) Sep 1988, 99-101.	
	CT1	HARENDT, C.; Hunt, C.; Appel, W.; Graf, H.-G.; Hofflinger, B.; Penteker, E., Silicon on Insulator Material by Wafer Bonding, J. Electronic Materials, 20(3) Mar 1991, 267-277.	
	CU1	HO, K.M.; Chan, C.T.; Soukoulis, C.M., Existence of a Photonic Gap in Periodic Dielectric Structures, Phys. Rev. Lett., 65(25) Dec 17, 1990, 3152-3155.	
	CV1	HOLLAND, Brian T.; Blanford, C.F.; Stein, A., Synthesis of Macroporous Minerals with Highly Ordered Three-Dimensional Arrays of Spheroidal Voids, Science, 281 Jul 24, 1998, 538-540.	
	CW1	IYER, S. Sundar Kumar, et al., Separation by Plasma Implantation of Oxygen (SPIMOX) Operational Phase Space, IEEE Transactions on Plasma Science, 25(5) Oct 1997, 1128-1135.	
	CX1	JENG, Shin-Puu; Chang, M.-C.; Kroger, T.; McAnally, P.; Havemann, R.H., A Planarized Multilevel Interconnect Scheme With Embedded Low-Dielectric-Constant Polymers For Sub-Quarter-Micron Applications, 1994 Symposium on VLSI Technology Digest of Technical Papers, 73-74.	
	CY1	JIANG, Peng; Ostojic, G.N.; Narat, R.; Mittleman, D.M.; Colvin, V.L., The Fabrication and Bandgap Engineering of Photonic Multilayers, Adv. Mater. 13(6) Mar 16, 2001, 389-393.	
	CZ1	JIN, C.; Lin, S.; Wetzel, J.T., Evaluation of Ultra-Low-k Dielectric Materials for Advanced Interconnects, J. Electronic Materials, 30(4) 2001, 284-289.	
	CA2	JOANNOPOULOS, John D.; Meade, R.D.; Winn, J.N., Photonic Crystals, Molding the Flow of Light, c1995, Princeton University Press, Princeton, NJ, 6.	
	CB2	JOHN, Sageev; Busch, K., Photonic Bandgap Formation and Tunability in Certain Self-Organizing Systems, J. Lightwave Technology, 17(11) Nov 1999, 1931-1943.	
	CC2	JOHNSON, Steven G.; Fan, S.; Villeneuve, P.R.; Joannopoulos, J.D.; Kolodziejski, L.A., Guided modes in photonic crystal slabs, Phys. Rev. B, 60(8), Aug 15, 1999, 5751-5758.	
	CD2	JURCZAK, M., et al., SON (Silicon On Nothing) - A New Device Architecture for the ULSI Era, 1999 Symposium on VLSI Technology Digest of Papers, 29-30.	
	CE2	KALAVADE, Pranav; Saraswat, K.C., A Novel sub-10nm Transistor, 58th DRC, Conf. Dig. Jun 19-21, 2000, 71-72.	
	CF2	KANG, J.S.; Schroder, D.K., Gettering in silicon, J. Appl. Phys., 65(8) Apr 15, 1989, 2974-2985.	
	CG2	KARUNASIRI, R.P.U.; Bruinsma, R.; Rudnik, J., Thin-Film Growth and the Shadow Instability, Phys. Rev. Lett., 62(7) Feb. 13, 1989, 788-791.	
	CH2	KINGERY, W.D., Introduction to Ceramics, (c1963), John Wiley & Sons, Inc., New York, 262-263.	
	CI2	KITTEL, Charles, Introduction to Solid State Physics, 3rd ed., (c1966) John Wiley & Sons, Inc., New York, 25.	
	CJ2	KOSTRZEWA, M., et al., Testing the Feasibility of Strain Relaxed Compliant Substrates, EMC 2003 Int'l Conf. Indium Phosphide and Related Materials, Jun, 8.	
	CK2	KUNG, C.Y.; Forbes, L.; Peng, J.D., The effect of carbon on oxygen precipitation in high carbon CZ silicon crystals, Mat. Res. Bull., Vol. 18, 1983, 1437-1441.	
	CL2	LASKY, J.B., Wafer bonding for silicon-on-insulator technologies, Appl. Phys. Lett., 48(1) Jan 6, 1986, 78-80.	
	CM2	LI, Zhi-Yuan; Zhang, Z.-Q., Photonic Bandgaps in Disordered Inverse-Opal Photonic Crystals, Adv. Mater. 13(6) Mar 16, 2001, 433-436.	
	CN2	LI, Y.X.; Liu, C.C.; Guo, H.Y.; Wang, X.; Pan, M.X.; Xu, Y.S.; Yang, D.R.; Que, D.L., New Intrinsic Gettering Process in Czochralski-silicon Wafer, 2001 6th Int'l Conf. on Solid-State and Integrated-Circuit Technology Proc., Vol. 1, Oct 22-25, Shanghai, CN, 277-279.	
	CO2	LIN, Shawn-Yu; Fleming, J.G., A Three-Dimensional Optical Photonic Crystal, J. Lightwave Technol., 17(11) Nov 1999, 1944-1947.	
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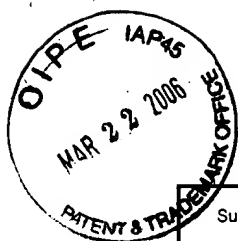
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			Art Unit	2828
			Examiner Name	A. Rodriguez
			Attorney Docket Number	M4065.0439/P439
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CP2	LONCAR, Marko; Nedeljkovic, D.; Doll, T.; Vuckovic, J.; Scherer, A.; Pearsall, T.P., Waveguiding in planar crystals, Appl. Phys. Lett., 77(13) Sep 25, 2000, 1937-1939.	
CQ2	LOO, Y.-L.; Willett, R.L.; Baldwin, K.W.; Rogers, J.A., Contact printing with nanometer resolution, 60th DRC, Jun 24-26, 2002, Santa Barbara, CA, 149-150.	
CR2	LU, Deren; Wortman, J.J.; Fathy, D., Bonding silicon wafers by use of electrostatic fields followed by rapid thermal heating, Materials Letters, 4(11,12) Oct 1986, 461-464.	
CS2	LU, Yu, Yin, Y.; Xia, Y., Three-Dimensional Photonic Crystals with Non-spherical Colloids as Building Blocks, Adv. Mater., 13(6) Mar 16, 2001, 415-420.	
CT2	MALAC, Marek; Brett, M., Thin Films Deposited at Glancing Incidence and their Applications, Vacuum Technology & Coating, July 2001, 48-53.	
CU2	MANOHARAN, Vinodhan N.; Imhof, A.; Thorne, J.D.; Pine, D.J., Photonic Crystals from Emulsion Templates, Adv. Mater., 13(6) Mar 16, 2001, 447-450.	
CW2	MESSIER, R.; Gehrke, T.; Frankel, C.; Venugopal, V.C.; Otano, W.; Lakhtakia, A., Engineered sculptured nematic thin films, J. Vac. Sci. Technol. A 15(4) Jul/Aug 1997, 2148-2152.	
CX2	MIGUEZ, Hernan; Meseguer, F.; Lopez, C.; Lopez-Tejiera, F.; Sanchez-Dehesa, J., Synthesis and Photonic Bandgap Characterization of Polymer Inverse Opals, Adv. Mater., 13(6) Mar 16, 2001, 393-396.	
CY2	MITSUTAKE, Kunihiro; Ushiku, Y., Theoretical Study on the Formation Process of Empty Space in Silicon (ESS), 2000 Int'l Conf. on Solid-State and Integrated Circuit Technol., 198-199.	
CZ2	MIZUNO, T.; Sugiyama, N.; Satake, H.; Takagi, S., Advanced SOI-MOSFETS with Strained-Si Channel for High Speed CMOS-Electron/Hole Mobility Enhancement, 2000 Symposium on VLSI Technol., Digest of Technical Papers, 210-211.	
CA3	MIZUSHIMA, I.; Sato, T.; Taniguchi, S.; Tsunashima, Y., Empty-space-in-silicon technique for fabricating a silicon-on-nothing structure, Appl. Phys. Lett., 77(20) Nov 13, 2000, 3290-3292.	
CB3	MOREY, George W., The Properties of Glass, 2nd ed., c1954, Reinhold Pub. Corp., New York, 12, 48-49.	
CC3	MUMOLA, P.B.; Gardopee, G.J.; Mathur, D.P.; Siniaguine, O., Recent advances in thinning of bonded SOI wafers by plasma assisted chemical etching, Proc.of the 3rd Int'l Symposium on Semiconductor Wafer Bonding: Physics and Applications, The Electrochemical Soc., 1995, Vols. 95-7, 28-32.	
CD3	NAYAK, D.K.; Park, J.S.; Woo, J.C.S.; Wang, K.L.; Yabiku, G.K.; MacWilliams, K.P., High Performance GeSi Quantum-Well PMOS on SIMOX, Int'l Electron Devices Meeting, 1992, 777-780.	
CE3	NEW SCIENTIST.com, Secret of 'strained silicon' chips revealed, Dec 17, 2003, <a href="http://www.newscientist.com/news/print.jsp?id=ns999944923">http://www.newscientist.com/news/print.jsp?id=ns999944923</a> 2 pages.	
CF3	NI, Peigen; Dong, P.; Cheng, B.; Li, X.; Zhang, D., Synthetic SiO <sub>2</sub> Opals, Adv. Mater., 13(6) Mar 16, 2001, 437-441.	
CG3	NORRIS, David J.; Vlasov, Y.A., Chemical Approaches to Three-Dimensional Semiconductor Photonic Crystals, Adv. Mater., 13(6) Mar 16, 2001, 371-376.	
CH3	OMI, Hiroo; Bottomley, D.; Ogino, T., Semiconductor Surface with Strain Control, <a href="http://www.brl.ntt.co.jp/J/kouhou/katsudou/report00/E/report04_e.html">http://www.brl.ntt.co.jp/J/kouhou/katsudou/report00/E/report04_e.html</a> one page	
CI3	O'NEILL, A.G.; Antoniadis, D.A., High speed deep sub-micron MOSFET using high mobility strained silicon channel, Proc. of the 25th European Solid State Device Res. Conf., Sep 25-27, 1995, The Hague, NL, 110-112.	
CJ3	OR, B.S.S.; Forbes, L.; Haddad, H.; Richling, W., Annealing Effects of Carbon in n-Channel LDD MOSFETS's, IEEE Electron Device Letters, 12(11) Nov 1991, 596-598.	
CK3	OUYANG, Q.; Chen, X.D.; Mudanai, S.; Kencke, D.L.; Tasch, A.F.; Banerjee, S.K., Bandgap Engineering in Deep Submicron Vertical pMOSFETs, 58th DRC, Conf. Digest, Jun 19-21,	
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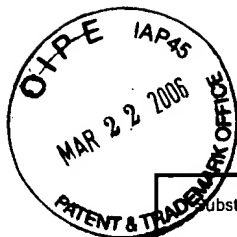
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			Art Unit	2828	
			Examiner Name	A. Rodriguez	
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		2000, 27-28.	
CL3	PAINE, D.C.; Howard, D.J.; Stoffel, N.G.; Horton, J.A., The growth of strained Si <sub>1-x</sub> Ge <sub>x</sub> alloys on (001) silicon using solid phase epitaxy, J. Mater. Res., 5(5) May 1990, 1023-1031.		
CM3	PANDYA, D.K.; Rastogi, A.C.; Chopra, K.L., Obliquely deposited amorphous Ge films. I. Growth and structure, J. Appl. Phys., 46(7) Jul 1975, 2966-2975.		
CN3	PEOPLE, R.; Bean, J.C., Calculation of critical layer thickness versus lattice mismatch for Ge <sub>x</sub> Si <sub>1-x</sub> /Si strained-layer heterostructures, Appl. Phys. Lett., 47(3) Aug 1, 1995, 322-324 (Erratum attached)		
CO3	RIM, Kern; Hoyt, J.L.; Gibbons, J.F., Fabrication and Analysis of Deep Submicron Strained-Si N-MOSFET's, IEEE Transactions on Electron Devices, 47(7) Jul 2000, 1406-1415.		
CP3	RIM, K, et al., Strained Si NMOSFETs for High Performance CMOS Technology, 2001 Symposium on VLSI Technol., Digest of Technical Papers, 59-60.		
CQ3	RIM, Kern; Hoyt, J.L.; Gibbons, J.F., Transconductance Enhancement in Deep Submicron Strained-Si n-MOSFETs, Int'l Electron Devices Meeting 1998, Technical Digest, 707-710		
CR3	ROBBIE, K.; Brett, M.J., Sculptured thin films and glancing angle deposition: Growth mechanics and applications, J. Vac. Sci. Technol. A 15(3) May/Jun 1997, 1460-1465.		
CS3	RUBIN, Leonard; Pech, R.; Huber, D.; Brunner, J.; Morris, W., Effective Gettering of Oxygen by High Dose, High Energy Boron Buried Layers, 1998 Int'l Conf. on Ion Implantation Technol. Proc., Kyoto, JP, Jun 22-26, 1010-1013.		
CT3	SATO, Tsutomu, et al., Trench Transformation Technology using Hydrogen Annealing for Realizing Highly Reliable Device Structure with Thin Dielectric Films, 1998 Symp. on VLSI Technol., Digest of Technical Papers, 206-207.		
CU3	SMITH, C.J.M., et al., Low-loss channel waveguides with two-dimensional photonic crystal boundaries, Appl. Phys. Lett., 77(18) Oct 30, 2000, 2813-2815.		
CV3	SUBRAMANIA, Ganapathi; Constant, K.; Biswas, R.; Sigalas, M.M.; Ho, K.-M., Inverse Face-Centered Cubic Thin Film Photonic Crystals, Adv. Mater. 13(6) Mar 16, 2001, 443-446.		
CW3	SUGIYAMA, N.; Mizuno, T.; Takagi, S.; Koike, M.; Kurobe, A., Formation of strained-silicon layer on thin relaxed-SiGe/SiO <sub>2</sub> /Si structure using SIMOX technology, Thin Solid Films, 369 (2000) 199-202.		
CX3	TAIT, R.N.; Smy, T.; Brett, M.J., Modelling and characterizations of columnar growth in evaporated films, Thin Solid Films, 236 (1993) 196-201.		
CY3	TAKAGI, Shin-ichi, Strained-Si- and SiGe-On-Insulator (Strained-SOI and SGOI) MOSFETs for High Performance/Low Power CMOS Application, IEEE 60th DRC, Conf. Digest (2002) 37-40.		
CZ3	TAN, T.Y.; Gardner, E.E.; Tice, W.K., Intrinsic gettering by oxide precipitate induced dislocations in Czochralski Si, Appl. Phys. Lett., 30(4) Feb 15, 1977, 175-176.		
CA4	TESSIER, P.M.; Velez, O.D.; Kalambur, A.T.; Lenhoff, A.M.; Rabolt, J.F.; Kaler, E.W., Structured Metallic Films for Optical and Spectroscopic Applications via Colloidal Crystal Templating, Adv. Mater. 13(6) Mar 16, 2001, 396-400.		
CB4	THORNTON, John A., High Rate Thick Film Growth, Ann. Rev. Mater. Sci., 7 (1977) 239-260.		
CC4	TREICHEL, H., Low Dielectric Constant Materials, J. Electronic Mater., 30(4) 2001, 290-298.		
CD4	VERDONCKT-VANDEBROEK, Sophie, et al., SiGe-Channel Heterojunction p-MOSFET's, IEEE Transactions on Electron Devices, 41(1) Jan 1994, 90-101.		
CE4	WELSER, J.; Hoyt, J.L.; Takagi, S.; Gibbons, J.F., Strain Dependence of the Performance Enhancement in Strained-Si n-MOSFETs, IEEE Int'l Electron Devices Meeting, Technical Digest, Dec 11-14, 1994, 373-376.		
CF4	WHITWER, F.D.; Haddad, H.; Forbes, L., DLTS Characterization of Precipitation Induced Microdefects, Mat. Res. Soc. Symp. Proc. 71, Apr 1986, 53-57.		
CG4	WIJARANAKULA, W.; Burke, P.M.; Forbes, L.; Matlock, J.H., Effect of pre- and postepitaxial deposition annealing on oxygen precipitation in silicon, J. Mater. Res. 1(5) Sep/Pct 1986, 698-		
Examiner Signature		Date Considered	



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Sheet	10	of	10		

		704.	
CH4	WIJARANAKULA, W.; Burke, P.; Forbes, L.; Matlock, J.H., Effect of Preanneal Heat Treatment on Precipitation in Epitaxial Silicon, Mat. Res. Soc. Symp. Proc., 71, Apr 1986, 139-144.		
CI4	WIJARANAKULA, W.; Burke, P.M.; Forbes, L., Internal gettering heat treatments and oxygen precipitation in epitaxial silicon wafers, J. Mater. Res., 1(5) Sep/Oct 1986, 693-697.		
CJ4	WIJARANAKULA, W.; Matlock, J.H.; Mollenkopf, H.; Burke, P.; Forbes, L., Oxygen Precipitation in P/P+(100) Epitaxial Silicon Material, J. Electrochemical Soc., 134(9) Sep 1987, 2310-2316.		
CK4	WILD, M., Laser Assisted Bonding of Silicon and Glass in Micro-System Technology, (2003) <a href="http://www.ilt.fraunhofer.de/ilt/php/default.php?id=100265&amp;lan=eng&amp;dat=2">http://www.ilt.fraunhofer.de/ilt/php/default.php?id=100265&amp;lan=eng&amp;dat=2</a> one page		
CL4	WOLCIK, J.; Simionescu, C.G.; Lennard, W.N.; Haugen, H.K.; Davies, J.A.; Mascher, P., Characterization of Silicon Oxynitride Thin Films Deposited by ECR-PECVD, 10th Canadian Semiconductor Technology Conf., Aug 13-17, 2001, 184.		
CM4	XIA, Younan, Photonic Crystals, Adv. Mater., 13(6) Mar 16, 2001, 369.		
CN4	XIA, Younan; Gates, B.; Li, Z.-Y., Self-Assembly Approaches to Three-Dimensional Photonic Crystals, Adv. Mater. 13(6) Mar 16, 2001, 409-413.		
CO4	XUAN, Peiqi; Kedzierski, J.; Subramanian, V.; Bokor, J.; King, T.-J.; Hu, C., 60nm Planarized Ultra-thin Body Solid Phase Epitaxy MOSFETs, IEEE 58th DRC Meeting. Conf. Digest, Jun 19-21, 2001, 67-68.		
CP4	YABLONOVITCH, Eli, Inhibited Spontaneous Emission in Solid-State Physics and Electronics, Physical Rev. Lett., 58(20) May 18, 1987, 2059-2062.		
CQ4	YABLONOVITCH, Eli; Gmitter, T.J.; Leung, K.M., Photonic Band Structure: The Face-Centered-Cubic Case Employing Nonspherical Atoms, Physical Rev. Lett., 67(17) Oct 21, 1991, 2295-2298.		
CR4	YANG, Deren; Fan, R.; Shen, Y.; Tian, D.; Li, L.; Que, D., Intrinsic gettering in nitrogen doped Czochralski crystal silicon, Proc. of the 6th Int'l Symp. High Purity Silicon VI, The Electrochemical Soc., Inc., 17, (2000) 357-361.		
CS4	YANG, Deren; Que, D., Nitrogen in Czochralski Silicon, 6th Int'l Conf. on Solid-State and Integrated Circuit Technol., 1(1) 2001, 255-260.		
CT4	YANG, Peidong; Rizvi, A.H.; Messer, B.; Chmelka, B.F.; Whitesides, G.M.; Stucky, G.D., Patterning Porous Oxides within Microchannel Networks, Adv. Mater., 13(6) Mar 16, 2001, 427-431.		
CU4	YIN, Haizhou, et al., High Ge-Content Relaxed Si <sub>1-x</sub> Ge <sub>x</sub> Layers by Relaxation on Compliant Substrate with Controlled Oxidation, Electronic Materials Conf., Santa Barbara, CA, Jun 2002, 8.		
CV4	ZHANG, F., et al., Nanoglass™ E Copper Damascene Processing for Etch, Clean and CMP, IEEE Int'l Interconnect Technol. Conf., (2001) 57-59.		
CW4	ZHU, Z.H., Ejeckam, F.E.; Zhang, Z.; Zhang, J.; Qian, Y.; Lo, Y.-H., 10th Ann. Meeting IEEE Lasers and Electro-Optics Soc., Conf. Proc., Nov 10-13, 1996, 31.		
CX4	ZHU, Z.-H., et al., Wafer Bonding Technology and Its Applications in Optoelectronic Devices and Materials, IEEE J. Selected Topics in Quantum Electronics, 3(3) Jun 1997, 927-936.		

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<sup>1</sup>Applicant's unique citation designation number (optional). <sup>2</sup>Applicant is to place a check mark here if English language Translation is attached.

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